

## Abstract

Method for etching a substrate wherein, after placing in an etching chamber, said substrate is treated with a mixture of HF and acetic acid. Acetic acid is introduced into the  
5 chamber first, followed by the hydrogen fluoride. Hydrogen fluoride is introduced via an intermediate stage during which the hydrogen fluoride is stored in an auxiliary chamber. By this means back-flow of a corrosive mixture consisting of hydrogen fluoride and acetic acid into the piping assembly for hydrogen fluoride is prevented and, thus, the life of the piping assembly concerned is appreciably prolonged and metal contamination on substrate treated  
10 later is prevented.

106270-0100